

REMARKS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1-22 are pending in the present application. Claims 1-15, 17-20 and 22 have been amended by the present amendment.

In the outstanding Office Action, Claims 1-22 were rejected under 35 U.S.C. § 112, second paragraph.

Applicant thanks the Examiner for discussing this application with Applicants' representative on June 24, 2003. During the discussion, the Examiner requested the claims and drawings be clarified to distinguish the difference between the first conductivity type semiconductor substrate (1) and the plurality of first conductivity type semiconductor regions (4) shown in Figure 1B, for example. In more detail, the Examiner indicated it appears from the figures that the semiconductor regions (4) are the same as the semiconductor substrate (1).

Accordingly, the claims have been amended to clearly recite that the semiconductor light-receiving device includes a semiconductor substrate, a semiconductor layer formed on a first surface of the semiconductor substrate, a plurality of first semiconductor regions formed in the semiconductor layer, and a second semiconductor region selectively formed in a surface region of the semiconductor layer. Claim 1 also recites that the semiconductor substrate comprises a first conductivity type, the plurality of first semiconductor regions comprise the first conductivity type, and the second semiconductor region comprises a second conductivity type.

As discussed in the specification, in the plural regions of the n⁻-type silicon layer 2, n⁺-type silicon regions 4 are formed by diffusion from the surface of the n⁻-type silicon layer 2 so as to reach the n⁺-type silicon substrate 1 by diffusion (see page 8, lines 1-5).

Application No. 09/813,827
Reply to Office Action dated July 14, 2003

Although the semiconductor substrate 1 and the silicon regions 4 include a same conductivity type, they are different regions of the device.

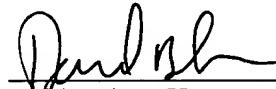
In addition, Figures 1B, 2E, 3B, 4B, 5B, 6B have been amended to clearly designate that the silicon regions 4 are different regions than the semiconductor substrate 1. Replacement drawings are included therewith.

Accordingly, it is respectfully requested the rejection of Claims 1-22 under 35 U.S.C. § 112, second paragraph, be withdrawn.

Consequently, in light of the above discussion and in view of the present amendment, the present application is believed to be in condition for allowance, and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Eckhard H. Kuesters
Attorney of Record
Registration No. 28,870
David A. Bilodeau
Registration No. 42,325



22850

Tel: (703) 413-3000
Fax: (703) 413 -2220
EHK:DAB/bwt

I:\ATTY\DAB\204404US-SUPPAM.DOC